



IN THE UNITED STATES PATENT
AND TRADEMARK OFFICE

Serial No. : 10/739,229)
Confirmation : 1123)
)
Applicants : CHO, Byoung H.)
Filed : December 18, 2003)
)
Title: METHOD FOR FORMING)
GATE OXIDE IN SEMICONDUCTOR)
DEVICE)
)
Art Unit : 2818)
Examiner : NHU, David)
)
Atty Docket : 29936/39870)
Customer No. : 04743)

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Michael Muczynski

COMMENTS ON STATEMENT OF REASONS FOR ALLOWANCE

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Sir:

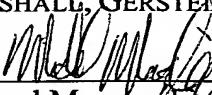
This paper is responsive to the "Reasons for Allowance" in the Notice of
Allowance and Fee(s) Due dated June 13, 2005, and is submitted under 37 C.F.R. § 1.104(e).

Consistent with MPEP 2111, during examination the U.S. Patent and
Trademark Office has given the claims their broadest reasonable interpretation as they would
be understood by one of ordinary skill in the art. In addition to the reasons set forth in the
allowance papers, it is respectfully submitted that the claims are allowable for the additional
reasons that the invention defined by the language of the claims is neither anticipated by, nor
would have been obvious when taken as a whole in view of, the art of record.

Respectfully submitted,

MARSHALL, GERSTEIN & BORUN LLP

By


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